

SKiiP 20 NAB 06 - SKiiP 20 NAB 06 I

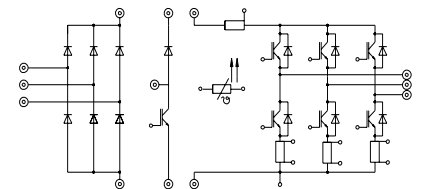
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Absolute Maximum Ratings		Values	Units
Symbol	Conditions ¹⁾		
Inverter			
V_{CES}		600	V
V_{GES}		± 20	V
I_C	$T_{\text{heatsink}} = 25 / 80 \text{ }^\circ\text{C}$	22 / 15	A
I_{CM}	$t_p < 1 \text{ ms}; T_{\text{heatsink}} = 25 / 80 \text{ }^\circ\text{C}$	44 / 30	A
$I_F = -I_C$	$T_{\text{heatsink}} = 25 / 80 \text{ }^\circ\text{C}$	36 / 24	A
$I_{FM} = -I_{CM}$	$t_p < 1 \text{ ms}; T_{\text{heatsink}} = 25 / 80 \text{ }^\circ\text{C}$	72 / 48	A
Bridge Rectifier			
V_{RRM}		800	V
I_D	$T_{\text{heatsink}} = 80 \text{ }^\circ\text{C}$	25	A
I_{FSM}	$t_p = 10 \text{ ms}; \sin. 180^\circ, T_j = 25 \text{ }^\circ\text{C}$	370	A
I^2t	$t_p = 10 \text{ ms}; \sin. 180^\circ, T_j = 25 \text{ }^\circ\text{C}$	680	A ² s
T_j		- 40 ... + 150	$^\circ\text{C}$
T_{stg}		- 40 ... + 125	$^\circ\text{C}$
V_{isol}	AC, 1 min.	2500	V

Characteristics		min.	typ.	max.	Units
Symbol	Conditions ¹⁾				
IGBT - Inverter & Chopper					
V_{CESat}	$I_C = 15 \text{ A}, T_j = 25 (125) \text{ }^\circ\text{C}$	-	2,1(2,2)	2,7(2,8)	V
$t_{d(on)}$	$V_{CC} = 300 \text{ V}; V_{GE} = \pm 15 \text{ V}$ $I_C = 15 \text{ A}; T_j = 125 \text{ }^\circ\text{C}$ $R_{gon} = R_{goff} = 68 \text{ }^\circ\Omega$ inductive load	-	35	70	ns
t_r		-	50	100	ns
$t_{d(off)}$		-	250	370	ns
t_f		-	500	750	ns
$E_{on} + E_{off}$		-	2,2	-	mJ
C_{ies}	$V_{CE} = 25 \text{ V}; V_{GE} = 0 \text{ V}, 1 \text{ MHz}$	-	0,8	-	nF
R_{thjh}	per IGBT	-	-	2,0	K/W
Diode ²⁾ - Inverter					
$V_F = V_{EC}$	$I_F = 25 \text{ A}, T_j = 25 (125) \text{ }^\circ\text{C}$	-	1,45(1,4)	1,7(1,7)	V
V_{TO}	$T_j = 125 \text{ }^\circ\text{C}$	-	0,85	0,9	V
r_T	$T_j = 125 \text{ }^\circ\text{C}$	-	22	32	m Ω
I_{RRM}	$I_F = 25 \text{ A}, V_R = -300 \text{ V}$ $di_F/dt = -500 \text{ A}/\mu\text{s}$ $V_{GE} = 0 \text{ V}, T_j = 125 \text{ }^\circ\text{C}$	-	25	-	A
Q_{rr}		-	2,5	-	μC
E_{off}		-	0,75	-	mJ
R_{thjh}		per diode	-	-	1,7
Diode ²⁾ - Chopper					
$V_F = V_{EC}$	$I_F = 10 \text{ A}, T_j = 25 (125) \text{ }^\circ\text{C}$	-	1,45(1,4)	1,7(1,7)	V
V_{TO}	$T_j = 125 \text{ }^\circ\text{C}$	-	0,85	0,9	V
r_T	$T_j = 125 \text{ }^\circ\text{C}$	-	55	80	m Ω
I_{RRM}	$I_F = 10 \text{ A}, V_R = -300 \text{ V}$ $di_F/dt = -200 \text{ A}/\mu\text{s}$ $V_{GE} = 0 \text{ V}, T_j = 125 \text{ }^\circ\text{C}$	-	13	-	A
Q_{rr}		-	1,5	-	μC
E_{off}		-	0,45	-	mJ
R_{thjh}		per diode	-	-	2,7
Diode - Rectifier					
V_F	$I_F = 25 \text{ A}, T_j = 25 \text{ }^\circ\text{C}$	-	1,2	-	V
R_{thjh}	per diode	-	-	2,6	K/W
Temperature Sensor					
R_{TS}	$T = 25 / 100 \text{ }^\circ\text{C}$		1000 / 1670		Ω
Mechanical Data					
M_1	case to heatsink, SI Units	2	-	2,5	Nm
Case	mechanical outline see page B 16 - 8		M2		

MiniSKiiP 2 SEMIKRON integrated intelligent Power SKiiP 20 NAB 06 SKiiP 20 NAB 06 I ³⁾ 3-phase bridge rectifier + braking chopper + 3-phase bridge inverter

Case M2



UL recognized file no. E63532

- specification of shunts and temperature sensor see part A
- common characteristics see page B16-3

Options

- also available with single phase rectifier (called 20 NEB 06 or 20 NEB 06 I³⁾)
- also available with faster IGBTs (type ... 063), data sheet on request

- ¹⁾ $T_{\text{heatsink}} = 25 \text{ }^\circ\text{C}$, unless otherwise specified
- ²⁾ CAL = Controlled Axial Lifetime Technology (soft and fast recovery)
- ³⁾ With integrated DC and/or AC shunts
- ⁴⁾ accuracy of pure shunt, please note that for DC shunt no separate sensing contact is used.

$R_{cs(dc)}$	5 % ⁴⁾	16,5 m Ω
$R_{cs(ac)}$	1 %	10 m Ω

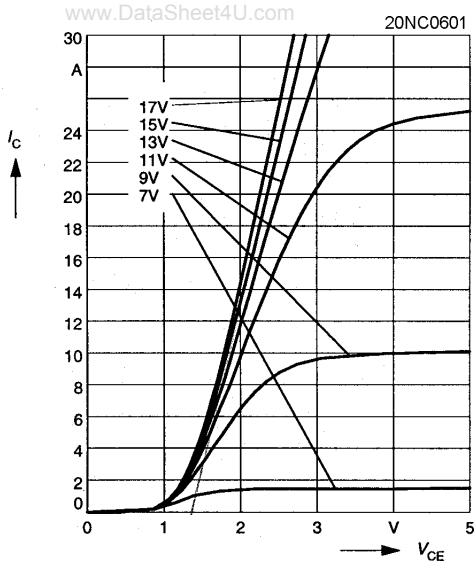


Fig. 1 Typ. output characteristic, $t_p = 80 \mu s$; $25 \text{ }^\circ\text{C}$

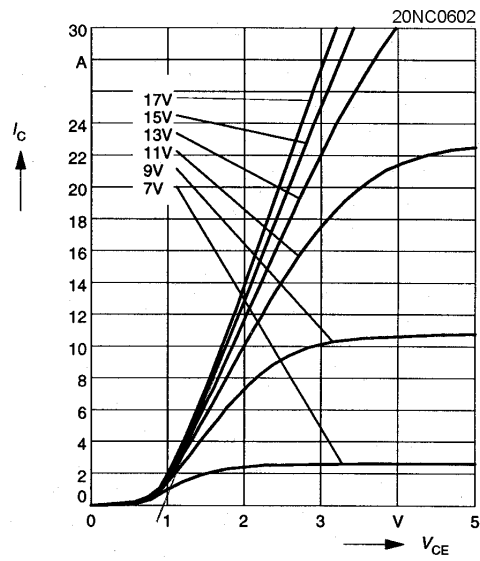


Fig. 2 Typ. output characteristic, $t_p = 80 \mu s$; $125 \text{ }^\circ\text{C}$

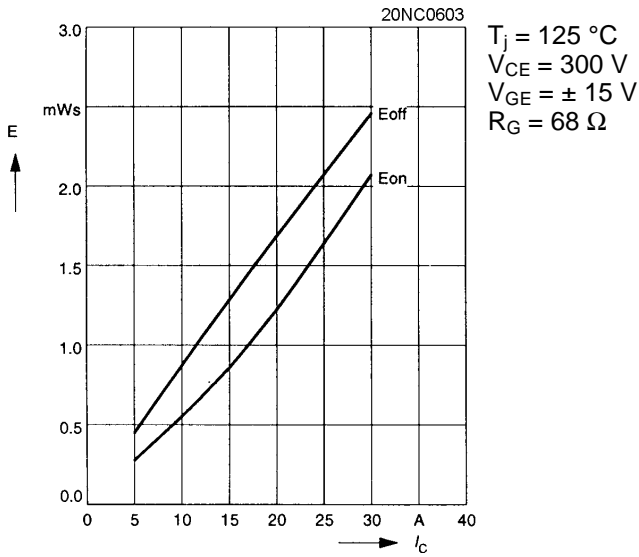


Fig. 3 Turn-on /-off energy = $f(I_c)$

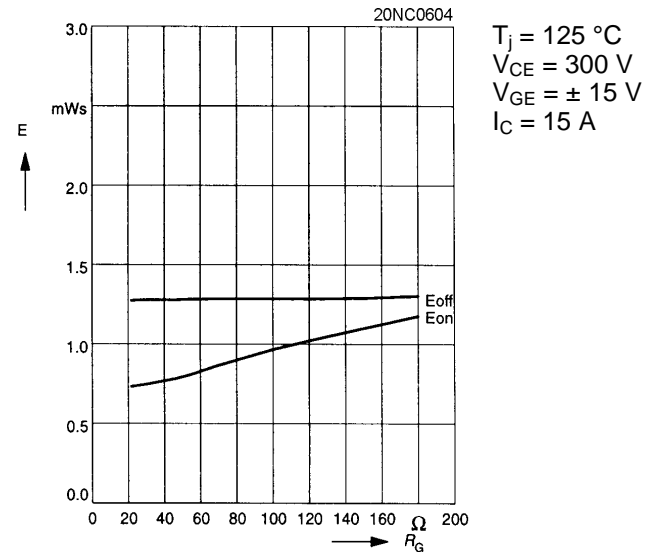


Fig. 4 Turn-on /-off energy = $f(R_G)$

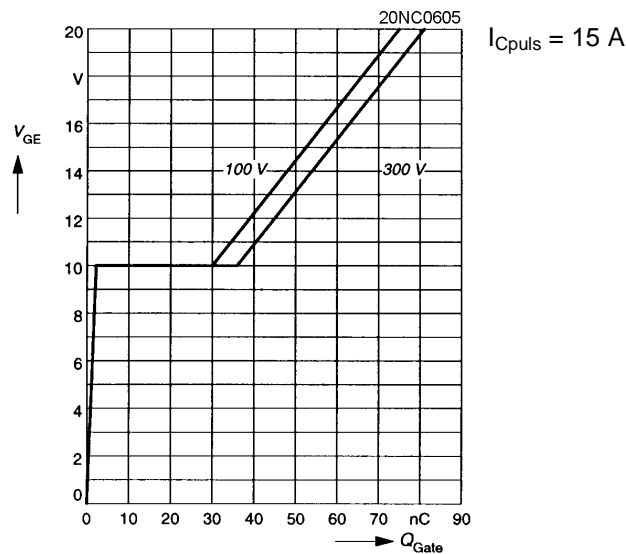


Fig. 5 Typ. gate charge characteristic

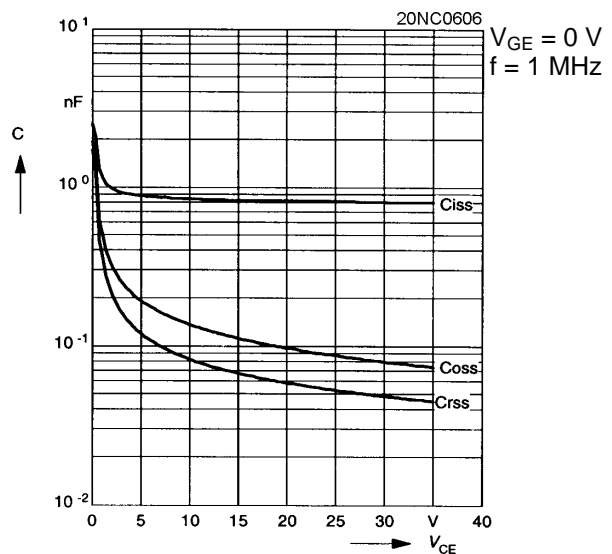


Fig. 6 Typ. capacitances vs. V_{CE}

2. Common characteristics of MiniSKiiP

MiniSKiiP 600 V

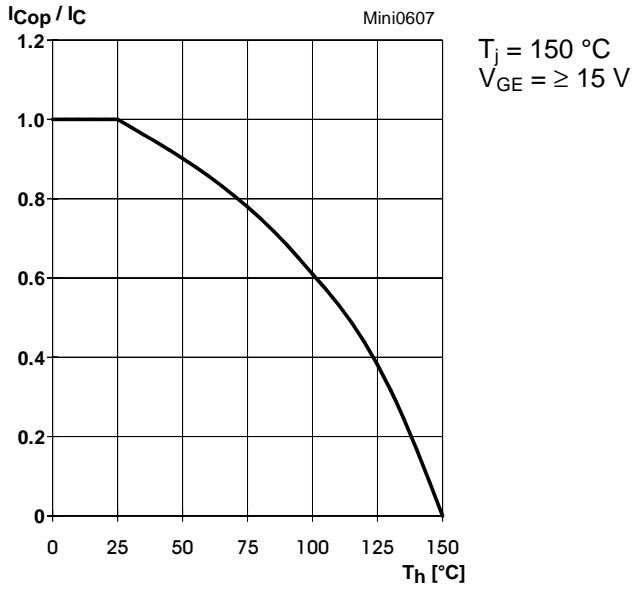


Fig. 7 Rated current of the IGBT $I_{COP} / I_C = f(T_h)$

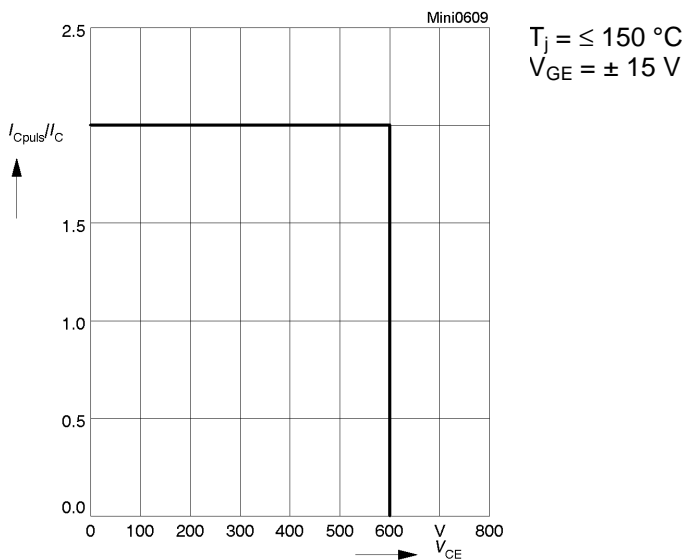


Fig. 9 Turn-off safe operating area (RBSOA) of the IGBT

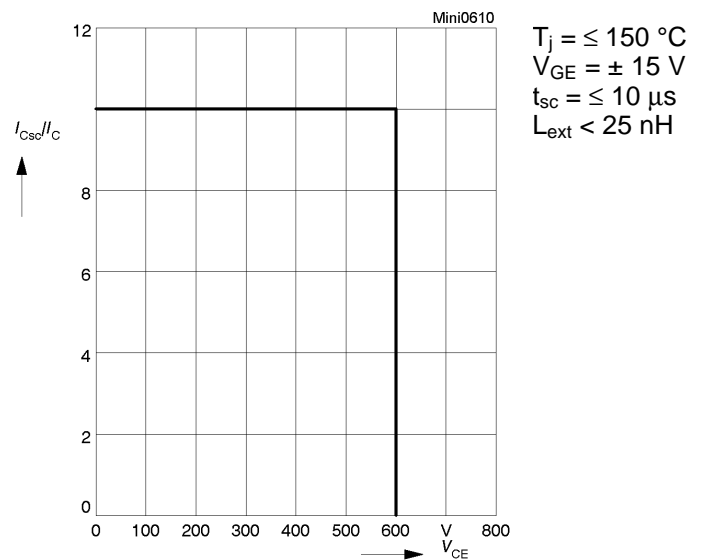


Fig. 10 Safe operating area at short circuit of the IGBT

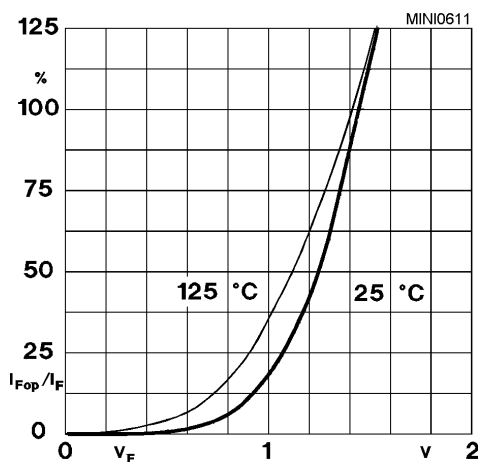


Fig. 11 Typ. freewheeling diode forward characteristic

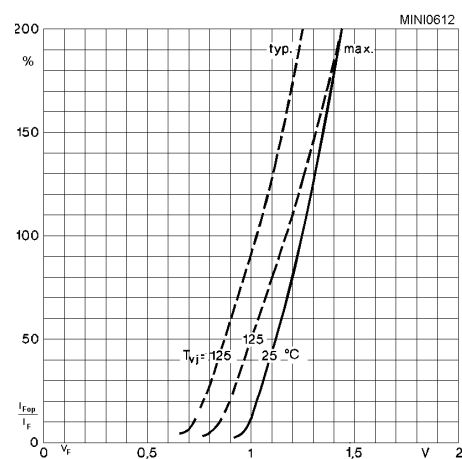


Fig. 12 Forward characteristic of the input bridge diode

MiniSKiiP 2

- SKiiP 20 NAB 06 ... Circuit
- SKiiP 21 NAB 06 ... Case M2
- SKiiP 20 NAB 12 ... Layout and connections for the customer's printed circuit board
- SKiiP 22 NAB 12 ...

Note: The shunts are available only by option I

